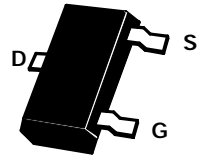


SOT23 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – DECEMBER 1995

ZVN4106F

PARMARKING DETAIL - MZ



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	0.2	A
Pulsed Drain Current	I_{DM}	3	A
Gate-Source Voltage	V_{GS}	± 20	V
Max Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

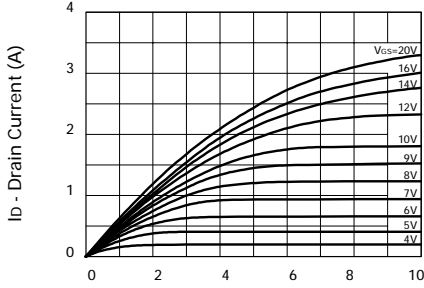
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60		V	$I_D=1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.3	3	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		10 50	μA μA	$V_{DS}=60V, V_{GS}=0$ $V_{DS}=48V, V_{GS}=0V, T=125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	1		A	$V_{DS}=25V, V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		2.5 5	Ω Ω	$V_{GS}=10V, I_D=500mA$ $V_{GS}=5V, I_D=200mA$
Forward Transconductance(1)(2)	g_{fs}	150		mS	$V_{DS}=25V, I_D=250mA$
Input Capacitance (2)	C_{iss}		35	pF	$V_{DS}=25V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		25	pF	
Reverse Transfer Capacitance (2)	C_{rss}		8	pF	
Turn-On Delay Time (2)(3)	$T_{d(on)}$		5	ns	$V_{DD}\approx 25V, I_D=150mA$
Rise Time (2)(3)	T_r		7	ns	
Turn-Off Delay Time (2)(3)	$T_{d(off)}$		6	ns	
Fall Time (2)(3)	T_f		8	ns	

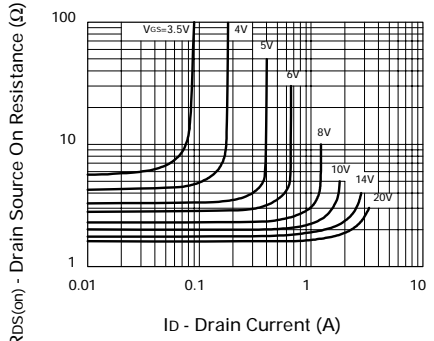
(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$ (2) Sample test.

(3) Switching times measured with 500 Ω source impedance and <5ns rise time on a pulse generator
Spice parameter data is available upon request for this device

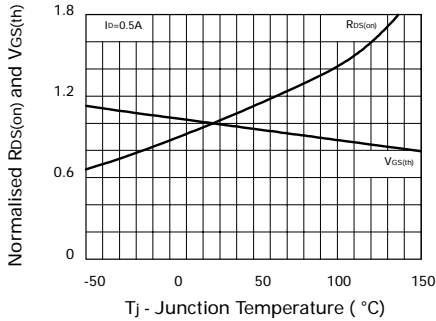
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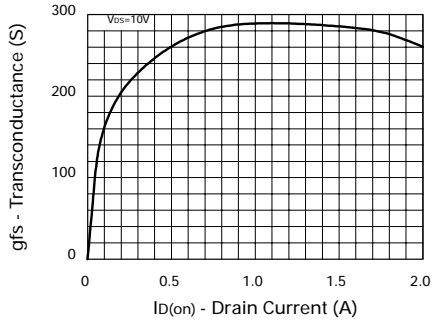
Saturation Characteristics



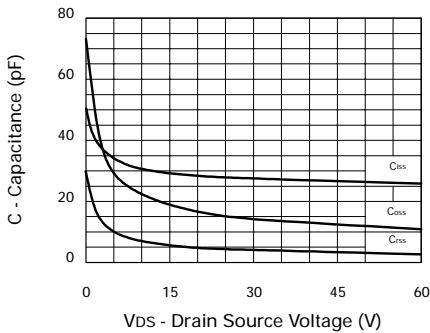
On-Resistance v Drain Current



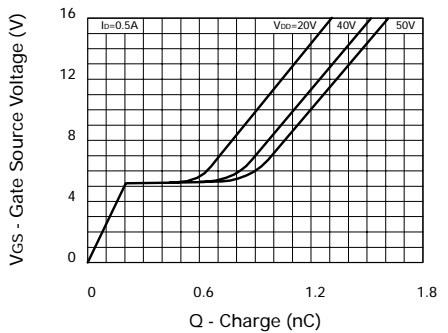
Normalised RDS(on) & VGS(th) v Temperature



Transconductance v Drain Current



Capacitance v Drain Source Voltage



Gate Source Voltage v Gate Charge